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Applications of "<u>Embedded - Microcontrollers</u>"

Details		
Product Status	Active	
Core Processor	ARM® Cortex®-M0	
Core Size	32-Bit Single-Core	
Speed	48MHz	
Connectivity	HDMI-CEC, I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART, USB	
Peripherals	DMA, I <sup>2</sup> S, POR, PWM, WDT	
Number of I/O	50	
Program Memory Size	128KB (128K x 8)	
Program Memory Type	FLASH	
EEPROM Size	-	
RAM Size	16K x 8	
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V	
Data Converters	A/D 19x12b; D/A 2x12b	
Oscillator Type	Internal	
Operating Temperature	-40°C ~ 85°C (TA)	
Mounting Type	Surface Mount	
Package / Case	64-LQFP	
Supplier Device Package	64-LQFP (10x10)	
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f078rbt6	

## **Contents**

1	Intro	uction	9
2	Desc	iption	0
3	Func	ional overview1	3
	3.1	ARM®-Cortex®-M0 core	13
	3.2	Memories	13
	3.3	Boot modes	13
	3.4	Cyclic redundancy check calculation unit (CRC)	14
	3.5	Power management	14
		3.5.1 Power supply schemes	14
		3.5.2 Power-on reset	14
		3.5.3 Low-power modes	14
	3.6	Clocks and startup	15
	3.7	General-purpose inputs/outputs (GPIOs)	16
	3.8	Direct memory access controller (DMA)	17
	3.9	Interrupts and events	17
		3.9.1 Nested vectored interrupt controller (NVIC)	17
		3.9.2 Extended interrupt/event controller (EXTI)	17
	3.10	Analog-to-digital converter (ADC)	17
		3.10.1 Temperature sensor	18
		3.10.2 Internal voltage reference (V <sub>REFINT</sub> )	18
		3.10.3 V <sub>BAT</sub> battery voltage monitoring	19
	3.11	Digital-to-analog converter (DAC)	19
	3.12	Comparators (COMP)	19
	3.13	Touch sensing controller (TSC)	19
	3.14	Timers and watchdogs	21
		3.14.1 Advanced-control timer (TIM1)	21
		3.14.2 General-purpose timers (TIM2, 3, 14, 15, 16, 17)	22
		3.14.3 Basic timers TIM6 and TIM7	23
		3.14.4 Independent watchdog (IWDG)	23
		3.14.5 System window watchdog (WWDG)	23
		3.14.6 SysTick timer	23

#### List of tables

Table 47.	ESD absolute maximum ratings	72
Table 48.	Electrical sensitivities	72
Table 49.	I/O current injection susceptibility	73
Table 50.	I/O static characteristics	73
Table 51.	Output voltage characteristics	76
Table 52.	I/O AC characteristics	77
Table 53.	NRST pin characteristics	79
Table 54.	NPOR pin characteristics	80
Table 55.	ADC characteristics	80
Table 56.	R <sub>AIN</sub> max for f <sub>ADC</sub> = 14 MHz	81
Table 57.	ADC accuracy	
Table 58.	DAC characteristics	84
Table 59.	Comparator characteristics	
Table 60.	TS characteristics	
Table 61.	V <sub>BAT</sub> monitoring characteristics	88
Table 62.	TIMx characteristics	
Table 63.	IWDG min/max timeout period at 40 kHz (LSI)	
Table 64.	WWDG min/max timeout value at 48 MHz (PCLK)	
Table 65.	I <sup>2</sup> C analog filter characteristics	
Table 66.	SPI characteristics	
Table 67.	I <sup>2</sup> S characteristics	
Table 68.	USB electrical characteristics	
Table 69.	UFBGA100 package mechanical data	
Table 70.	UFBGA100 recommended PCB design rules	
Table 71.	LQPF100 package mechanical data	
Table 72.	LQFP64 package mechanical data	
Table 73.	WLCSP49 package mechanical data	
Table 74.	LQFP48 package mechanical data	
Table 75.	UFQFPN48 package mechanical data	
Table 76.	Package thermal characteristics	
Table 77.	Ordering information scheme	
Table 78.	Document revision history	118



## List of figures

Figure 1.	Block diagram	12
Figure 2.	Clock tree	
Figure 3.	UFBGA100 package pinout	28
Figure 4.	LQFP100 package pinout	29
Figure 5.	LQFP64 package pinout	30
Figure 6.	LQFP48 package pinout	30
Figure 7.	UFQFPN48 package pinout	31
Figure 8.	WLCSP49 package pinout	31
Figure 9.	STM32F078CB/RB/VB memory map	43
Figure 10.	Pin loading conditions	46
Figure 11.	Pin input voltage	46
Figure 12.	Power supply scheme	47
Figure 13.	Current consumption measurement scheme	48
Figure 14.	High-speed external clock source AC timing diagram	62
Figure 15.	Low-speed external clock source AC timing diagram	
Figure 16.	Typical application with an 8 MHz crystal	
Figure 17.	Typical application with a 32.768 kHz crystal	
Figure 18.	HSI oscillator accuracy characterization results for soldered parts	66
Figure 19.	HSI14 oscillator accuracy characterization results	
Figure 20.	HSI48 oscillator accuracy characterization results	68
Figure 21.	TC and TTa I/O input characteristics	
Figure 22.	Five volt tolerant (FT and FTf) I/O input characteristics	
Figure 23.	I/O AC characteristics definition	
Figure 24.	Recommended NRST pin protection	79
Figure 25.	ADC accuracy characteristics	
Figure 26.	Typical connection diagram using the ADC	83
Figure 27.	12-bit buffered / non-buffered DAC	
Figure 28.	Maximum V <sub>REFINT</sub> scaler startup time from power down	
Figure 29.	SPI timing diagram - slave mode and CPHA = 0	
Figure 30.	SPI timing diagram - slave mode and CPHA = 1	
Figure 31.	SPI timing diagram - master mode	
Figure 32.	I <sup>2</sup> S slave timing diagram (Philips protocol)	
Figure 33.	I <sup>2</sup> S master timing diagram (Philips protocol)	
Figure 34.	UFBGA100 package outline	
Figure 35.	Recommended footprint for UFBGA100 package	
Figure 36.	UFBGA100 package marking example	
Figure 37.	LQFP100 package outline	
Figure 38.	Recommended footprint for LQFP100 package	
Figure 39.	LQFP100 package marking example	
Figure 40.	LQFP64 package outline	
Figure 41.	Recommended footprint for LQFP64 package	
Figure 42.	LQFP64 package marking example	
Figure 43.	WLCSP49 package outline	
Figure 44.	WLCSP49 package marking example	
Figure 45.	LQFP48 package outline	
Figure 46.	Recommended footprint for LQFP48 package	
Figure 47.	LQFP48 package marking example	
Figure 48.	UFQFPN48 package outline	



## 2 Description

The STM32F078CB/RB/VB microcontrollers incorporate the high-performance ARM<sup>®</sup> Cortex<sup>®</sup>-M0 32-bit RISC core operating at up to 48 MHz frequency, high-speed embedded memories (128 Kbytes of Flash memory and 16 Kbytes of SRAM), and an extensive range of enhanced peripherals and I/Os. All devices offer standard communication interfaces (two I<sup>2</sup>Cs, two SPI/I<sup>2</sup>S, one HDMI CEC and four USARTs), one USB Full-speed device (crystalless), one 12-bit ADC, one 12-bit DAC with two channels, seven 16-bit timers, one 32-bit timer and an advanced-control PWM timer.

The STM32F078CB/RB/VB microcontrollers operate in the -40 to +85  $^{\circ}$ C and -40 to +105  $^{\circ}$ C temperature ranges from a 1.8 V  $\pm$  8% power supply. A comprehensive set of power-saving modes allows the design of low-power applications.

The STM32F078CB/RB/VB microcontrollers include devices in six different packages ranging from 48 pins to 100 pins with a die form also available upon request. Depending on the device chosen, different sets of peripherals are included.

These features make the STM32F078CB/RB/VB microcontrollers suitable for a wide range of applications such as application control and user interfaces, hand-held equipment, A/V receivers and digital TV, PC peripherals, gaming and GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms and HVACs.

**577** 

sensor, voltage reference, VBAT voltage measurement) channels and performs conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

#### 3.10.1 Temperature sensor

The temperature sensor (TS) generates a voltage  $V_{\text{SENSE}}$  that varies linearly with temperature.

The temperature sensor is internally connected to the ADC\_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at a temperature of 30 °C (± 5 °C), V <sub>DDA</sub> = 3.3 V (± 10 mV)	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at a temperature of 110 °C (± 5 °C), V <sub>DDA</sub> = 3.3 V (± 10 mV)	0x1FFF F7C2 - 0x1FFF F7C3

Table 2. Temperature sensor calibration values

## 3.10.2 Internal voltage reference (V<sub>REFINT</sub>)

The internal voltage reference ( $V_{REFINT}$ ) provides a stable (bandgap) voltage output for the ADC and comparators.  $V_{REFINT}$  is internally connected to the ADC\_IN17 input channel. The precise voltage of  $V_{REFINT}$  is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 3. Internal voltage reference calibration values

Calibration value name	Description	Memory address
	Raw data acquired at a temperature of 30 °C (± 5 °C), V <sub>DDA</sub> = 3.3 V (± 10 mV)	0x1FFF F7BA - 0x1FFF F7BB



The RTC is an independent BCD timer/counter. Its main features are the following:

- calendar with subseconds, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- automatic correction for 28, 29 (leap year), 30, and 31 day of the month
- programmable alarm with wake up from Stop mode capability
- Periodic wakeup unit with programmable resolution and period.
- on-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize the RTC with a master clock
- digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- Three anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop mode on tamper event detection
- timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop mode on timestamp event detection
- reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision

The RTC clock sources can be:

- a 32.768 kHz external crystal
- a resonator or oscillator
- the internal low-power RC oscillator (typical frequency of 40 kHz)
- the high-speed external clock divided by 32

## 3.16 Inter-integrated circuit interface (I<sup>2</sup>C)

Up to two I<sup>2</sup>C interfaces (I2C1 and I2C2) can operate in multimaster or slave modes. Both can support Standard mode (up to 100 kbit/s), Fast mode (up to 400 kbit/s) and Fast Mode Plus (up to 1 Mbit/s) with extra output drive on most of the associated I/Os.

Both support 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (two addresses, one with configurable mask). They also include programmable analog and digital noise filters.

Table 7. Comparison of I<sup>2</sup>C analog and digital filters

Aspect	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2Cx peripheral clocks
Benefits	Available in Stop mode	<ul><li>–Extra filtering capability vs.</li><li>standard requirements</li><li>–Stable length</li></ul>
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

In addition, I2C1 provides hardware support for SMBUS 2.0 and PMBUS 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts



USART modes/features <sup>(1)</sup>	USART1 and USART2	USART3 and USART4
IrDA SIR ENDEC block	Х	-
LIN mode	Х	-
Dual clock domain and wakeup from Stop mode	Х	-
Receiver timeout interrupt	X	-
Modbus communication	X	-
Auto baud rate detection	Х	-
Driver Enable	Х	Х

Table 9. STM32F078CB/RB/VB USART implementation (continued)

# 3.18 Serial peripheral interface (SPI) / Inter-integrated sound interface (I<sup>2</sup>S)

Two SPIs are able to communicate up to 18 Mbit/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

Two standard I<sup>2</sup>S interfaces (multiplexed with SPI1 and SPI2 respectively) supporting four different audio standards can operate as master or slave at half-duplex communication mode. They can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by an 8-bit programmable linear prescaler. When operating in master mode, they can output a clock for an external audio component at 256 times the sampling frequency.

Table 10. STM32F078CB/RB/VB SPI/I<sup>2</sup>S implementation

SPI features <sup>(1)</sup>	SPI1 and SPI2
Hardware CRC calculation	Х
Rx/Tx FIFO	Х
NSS pulse mode	Х
I <sup>2</sup> S mode	Х
TI mode	Х

<sup>1.</sup> X = supported.

# 3.19 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The device embeds a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory



<sup>1.</sup> X = supported.

### 6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 20: Voltage characteristics*, *Table 21: Current characteristics* and *Table 22: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 20. Voltage characteristics<sup>(1)</sup>

Symbol	Ratings	Min	Max	Unit
V <sub>DD</sub> -V <sub>SS</sub>	External main supply voltage	-0.3	1.95	V
V <sub>DDIO2</sub> -V <sub>SS</sub>	External I/O supply voltage	- 0.3	4.0	V
V <sub>DDA</sub> -V <sub>SS</sub>	External analog supply voltage	- 0.3	4.0	V
V <sub>DD</sub> -V <sub>DDA</sub>	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
V <sub>BAT</sub> -V <sub>SS</sub>	External backup supply voltage	- 0.3	4.0	V
	Input voltage on FT and FTf pins	V <sub>SS</sub> -0.3	V <sub>DDIOx</sub> + 4.0 <sup>(3)</sup>	V
	Input voltage on POR pins	V <sub>SS</sub> -0.3	4.0	V
$V_{IN}^{(2)}$	Input voltage on TTa pins	V <sub>SS</sub> -0.3	4.0	V
	воото	0	9.0	V
	Input voltage on any other pin	V <sub>SS</sub> -0.3	4.0	V
ΔV <sub>DDx</sub>	Variations between different V <sub>DD</sub> power pins	-	50	mV
V <sub>SSx</sub> - V <sub>SS</sub>	Variations between all the different ground pins	-	50	mV
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	see Section 6.3.11: Electrical sensitivity characteristics		-

All main power (V<sub>DD</sub>, V<sub>DDA</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supply, in the permitted range.

V<sub>IN</sub> maximum must always be respected. Refer to Table 21: Current characteristics for the maximum allowed injected current values.

<sup>3.</sup> Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

**Table 21. Current characteristics** 

Symbol	Ratings	Max.	Unit
ΣI <sub>VDD</sub>	Total current into sum of all VDD power lines (source) <sup>(1)</sup>	120	
ΣI <sub>VSS</sub>	Total current out of sum of all VSS ground lines (sink) <sup>(1)</sup>	-120	
I <sub>VDD(PIN)</sub>	Maximum current into each VDD power pin (source) <sup>(1)</sup>	100	
I <sub>VSS(PIN)</sub>	Maximum current out of each VSS ground pin (sink) <sup>(1)</sup>	-100	
	Output current sunk by any I/O and control pin	25	
I <sub>IO(PIN)</sub>	Output current source by any I/O and control pin	-25	
	Total output current sunk by sum of all I/Os and control pins <sup>(2)</sup>	80	
$\Sigma I_{IO(PIN)}$	Total output current sourced by sum of all I/Os and control pins <sup>(2)</sup>	-80	mA
	Total output current sourced by sum of all I/Os supplied by VDDIO2	-40	
	Injected current on POR, B, FT and FTf pins	-5/+0 <sup>(4)</sup>	
I <sub>INJ(PIN)</sub> <sup>(3)</sup>	Injected current on TC and RST pin	± 5	1
	Injected current on TTa pins <sup>(5)</sup>	± 5	
ΣΙ <sub>ΙΝJ(PIN)</sub>	Total injected current (sum of all I/O and control pins) <sup>(6)</sup>	± 25	

- 1. All main power (VDD, VDDA) and ground (VSS, VSSA) pins must always be connected to the external power supply, in the permitted range.
- 2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
- 3. A positive injection is induced by  $V_{IN} > V_{DDIOx}$  while a negative injection is induced by  $V_{IN} < V_{SS}$ .  $I_{INJ(PIN)}$  must never be exceeded. Refer to *Table 20: Voltage characteristics* for the maximum allowed input voltage values.
- 4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
- On these I/Os, a positive injection is induced by V<sub>IN</sub> > V<sub>DDA</sub>. Negative injection disturbs the analog performance of the device. See note <sup>(2)</sup> below *Table 57: ADC accuracy*.
- When several inputs are submitted to a current injection, the maximum ΣI<sub>INJ(PIN)</sub> is the absolute sum of the positive and negative injected currents (instantaneous values).

**Table 22. Thermal characteristics** 

Symbol	Ratings	Value	Unit
T <sub>STG</sub>	Storage temperature range	-65 to +150	°C
T <sub>J</sub>	Maximum junction temperature	150	°C



#### **Typical current consumption**

The MCU is placed under the following conditions:

- V<sub>DD</sub> = V<sub>DDA</sub> = 1.8 V
- All I/O pins are in analog input configuration
- The Flash memory access time is adjusted to f<sub>HCLK</sub> frequency:
  - 0 wait state and Prefetch OFF from 0 to 24 MHz
  - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled, f<sub>PCLK</sub> = f<sub>HCLK</sub>
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8 and 16 is used for the frequencies 4 MHz, 2 MHz, 1 MHz and 500 kHz respectively

Table 29. Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal

Symbol	Parameter	•	Typical con Run	sumption in mode		sumption in mode	Unit
Symbol Paramete	raiailletei	Peripher	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Offic
		48 MHz	22.0	12.7	14.2	3.2	
	Current	36 MHz	17.1	9.9	10.8	2.5	
		32 MHz	15.4	8.9	9.7	2.2	
		24 MHz	11.9	7.0	7.5	1.8	
I <sub>DD</sub>	consumption	16 MHz	8.3	4.9	5.2	1.3	mA
טטי	from V <sub>DD</sub> supply	8 MHz	4.4	2.7	2.7	0.7	ША
	Зирріу	4 MHz	2.7	1.7	1.8	0.6	
		2 MHz	1.6	1.1	1.2	0.6	
		1 MHz	1.1	0.8	0.9	0.5	
		500 kHz	0.9	0.7	0.8	0.5	
		48 MHz		14	43		
		36 MHz		11	12		
		32 MHz	102				
	Current	24 MHz		8	1		
I== .	consumption	16 MHz		5	9		μA
DDA	I <sub>DDA</sub> from V <sub>DDA</sub> supply	8 MHz	1				
	Зирріу	4 MHz		1			
		2 MHz			1		
		1 MHz			1		
		500 kHz			1		

Table 32. Peripheral current consumption (continued)

	Peripheral	Typical consumption at 25 °C	Unit
	APB-Bridge <sup>(2)</sup>	2.8	
	ADC <sup>(3)</sup>	4.1	
	CEC	1.5	
	CRS	0.8	
	DAC <sup>(3)</sup>	4.7	
	DEBUG (MCU debug feature)	0.1	
	I2C1	3.9	
	I2C2	4.0	
	PWR	1.3	
	SPI1	8.7	
	SPI2	8.5	
	SYSCFG & COMP	1.7	
	TIM1	14.9	
	TIM2	15.5	
	TIM3	11.4	
APB	TIM6	2.5	µA/MHz
	TIM7	2.3	
	TIM14	5.3	
	TIM15	9.1	
	TIM16	6.6	
	TIM17	6.8	
	USART1	17.0	
	USART2	16.7	
	USART3	5.4	
	USART4	5.4	
	USB	7.2	
	WWDG	1.4	
	All APB peripherals	169.6	

<sup>1.</sup> The BusMatrix is automatically active when at least one master is ON (CPU, DMA).

<sup>2.</sup> The APB Bridge is automatically active when at least one peripheral is ON on the Bus.

<sup>3.</sup> The power consumption of the analog part  $(I_{DDA})$  of peripherals such as ADC, DAC, Comparators, is not included. Refer to the tables of characteristics in the subsequent sections.

#### 6.3.5 Wakeup time from low-power mode

The wakeup times given in *Table 33* are the latency between the event and the execution of the first user instruction. The device goes in low-power mode after the WFE (Wait For Event) instruction, in the case of a WFI (Wait For Interruption) instruction, 16 CPU cycles must be added to the following timings due to the interrupt latency in the Cortex M0 architecture.

The SYSCLK clock source setting is kept unchanged after wakeup from Sleep mode. During wakeup from Stop mode, SYSCLK takes the default setting: HSI 8 MHz.

The wakeup source from Sleep and Stop mode is an EXTI line configured in event mode.

All timings are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

		-			
Symbol	Parameter -		V <sub>DDA</sub>	Max	Unit
Symbol			= 3.3 V		
t <sub>WUSTOP</sub>	Wakeup from Stop mode	3.5	2.8	5.3	μs
t <sub>WUSLEEP</sub>	Wakeup from Sleep mode	4 SYSCI	K cycles	-	μs

Table 33. Low-power mode wakeup timings

#### 6.3.6 External clock source characteristics

#### High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in Section 6.3.13. However, the recommended clock input waveform is shown in Figure 14: High-speed external clock source AC timing diagram.

Symbol	Parameter <sup>(1)</sup>	Min	Тур	Max	Unit
f <sub>HSE_ext</sub>	User external clock source frequency	-	8	32	MHz
V <sub>HSEH</sub>	OSC_IN input pin high level voltage	0.7 V <sub>DDIOx</sub>	-	$V_{DDIOx}$	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage	V <sub>SS</sub>	-	0.3 V <sub>DDIOx</sub>	V
t <sub>w(HSEH)</sub>	OSC_IN high or low time	15	ı	-	ns
$\begin{matrix} t_{r(\text{HSE})} \\ t_{f(\text{HSE})} \end{matrix}$	OSC_IN rise or fall time	-	-	20	113

Table 34. High-speed external user clock characteristics

<sup>1.</sup> Guaranteed by design, not tested in production.

#### Low-speed internal (LSI) RC oscillator

Table 41. LSI oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Тур	Max	Unit
f <sub>LSI</sub>	Frequency	30	40	50	kHz
t <sub>su(LSI)</sub> <sup>(2)</sup>	LSI oscillator startup time	-	-	85	μs
I <sub>DDA(LSI)</sub> <sup>(2)</sup>	LSI oscillator power consumption	-	0.75	1.2	μΑ

<sup>1.</sup>  $V_{DDA}$  = 3.3 V,  $T_{A}$  = -40 to 105 °C unless otherwise specified.

#### 6.3.8 PLL characteristics

The parameters given in *Table 42* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 23: General operating conditions*.

**Table 42. PLL characteristics** 

Symbol	Parameter		Unit		
Symbol	Farameter	Min	Тур	Max	Offic
f	PLL input clock <sup>(1)</sup>	1 <sup>(2)</sup>	8.0	24 <sup>(2)</sup>	MHz
f <sub>PLL_IN</sub>	PLL input clock duty cycle	40 <sup>(2)</sup>	-	60 <sup>(2)</sup>	%
f <sub>PLL_OUT</sub>	PLL multiplier output clock	16 <sup>(2)</sup>	-	48	MHz
t <sub>LOCK</sub>	PLL lock time	-	-	200 <sup>(2)</sup>	μs
Jitter <sub>PLL</sub>	Cycle-to-cycle jitter	-	-	300 <sup>(2)</sup>	ps

Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f<sub>PLL OUT</sub>.

#### 6.3.9 Memory characteristics

#### Flash memory

The characteristics are given at  $T_A$  = -40 to 105 °C unless otherwise specified.

Table 43. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max <sup>(1)</sup>	Unit
t <sub>prog</sub>	16-bit programming time	T <sub>A</sub> = - 40 to +105 °C	40	53.5	60	μs
t <sub>ERASE</sub>	Page (2 KB) erase time	T <sub>A</sub> = - 40 to +105 °C	20	-	40	ms
t <sub>ME</sub>	Mass erase time	T <sub>A</sub> = - 40 to +105 °C	20	-	40	ms
I Supply current		Write mode	-	-	10	mA
IDD	Supply current	Erase mode	-	-	12	mA

<sup>1.</sup> Guaranteed by design, not tested in production.



<sup>2.</sup> Guaranteed by design, not tested in production.

<sup>2.</sup> Guaranteed by design, not tested in production.

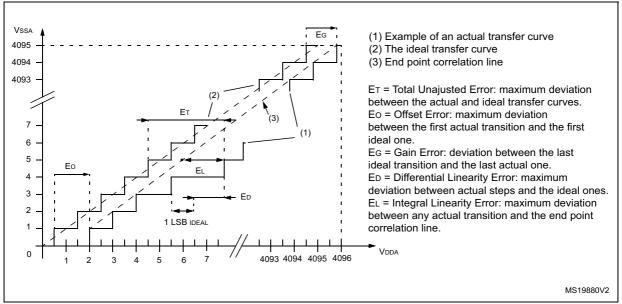
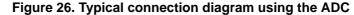
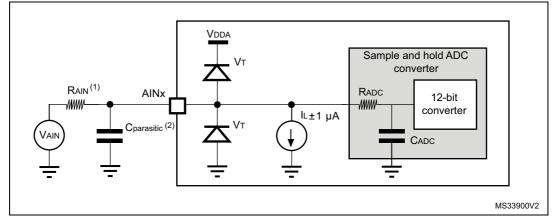


Figure 25. ADC accuracy characteristics





- Refer to *Table 55: ADC characteristics* for the values of R<sub>AIN</sub>, R<sub>ADC</sub> and C<sub>ADC</sub>.
- $C_{parasitic}$  represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high  $C_{parasitic}$  value will downgrade conversion accuracy. To remedy this,  $f_{ADC}$  should be reduced.

#### General PCB design guidelines

Power supply decoupling should be performed as shown in Figure 12: Power supply scheme. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

40

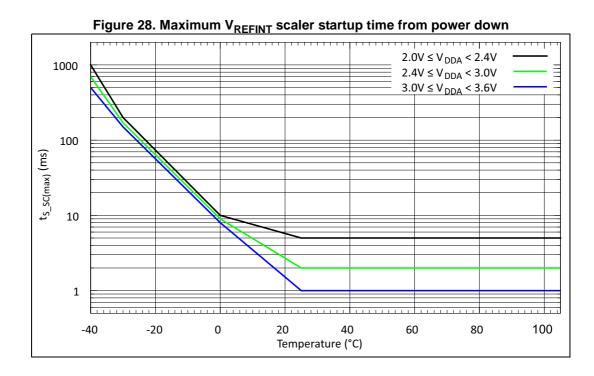
19

Min<sup>(1)</sup> Max<sup>(1)</sup> **Symbol** Тур Unit **Parameter Conditions** No hysteresis 0 (COMPxHYST[1:0]=00) High speed mode 3 13 Low hysteresis 8 All other power (COMPxHYST[1:0]=01) 5 10 modes Comparator hysteresis High speed mode 7 26 mV  $V_{hys}$ Medium hysteresis 15 All other power (COMPxHYST[1:0]=10) 9 19 modes High speed mode 18 49 High hysteresis 31 All other power

Table 59. Comparator characteristics (continued)

- 1. Data based on characterization results, not tested in production.
- 2. For more details and conditions see Figure 28: Maximum V<sub>REFINT</sub> scaler startup time from power down.

(COMPxHYST[1:0]=11)



modes

#### **USB** characteristics

The STM32F078CB/RB/VB USB interface is fully compliant with the USB specification version 2.0 and is USB-IF certified (for Full-speed device operation).

Table 68. USB electrical characteristics

Symbol	Parameter	Conditions	Min.	Тур	Max.	Unit
V <sub>DDIO2</sub>	USB transceiver operating voltage	-	3.0 <sup>(1)</sup>	-	3.6	V
t <sub>STARTUP</sub> (2)	USB transceiver startup time	-	-	-	1.0	μs
R <sub>PUI</sub>	Embedded USB_DP pull-up value during idle	-	1.1	1.26	1.5	kΩ
R <sub>PUR</sub>	Embedded USB_DP pull-up value during reception	-	2.0	2.26	2.6	K12
Z <sub>DRV</sub> <sup>(2)</sup>	Output driver impedance <sup>(3)</sup>	Driving high and low	28	40	44	Ω

<sup>1.</sup> The STM32F078CB/RB/VB USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V voltage range.



<sup>2.</sup> Guaranteed by design, not tested in production.

<sup>3.</sup> No external termination series resistors are required on USB\_DP (D+) and USB\_DM (D-); the matching impedance is already included in the embedded driver.

Table 74. LQFP48 package mechanical data

Symbol		millimeters			inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
Е	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
CCC	-	-	0.080	-	-	0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

9.70 ai14911d

Figure 46. Recommended footprint for LQFP48 package

1. Dimensions are expressed in millimeters.

As applications do not commonly use the STM32F078CB/RB/VB at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

#### **Example 1: High-performance application**

Assuming the following application conditions:

Maximum temperature  $T_{Amax}$  = 82 °C (measured according to JESD51-2),  $I_{DDmax}$  = 50 mA,  $V_{DD}$  = 3.5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$ = 0.4 V and maximum 8 I/Os used at the same time in output at low level with  $I_{OL}$  = 20 mA,  $V_{OL}$ = 1.3 V

 $P_{INTmax} = 50 \text{ mA} \times 3.5 \text{ V} = 175 \text{ mW}$ 

 $P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4 \text{ V} + 8 \times 20 \text{ mA} \times 1.3 \text{ V} = 272 \text{ mW}$ 

This gives: P<sub>INTmax</sub> = 175 mW and P<sub>IOmax</sub> = 272 mW:

 $P_{Dmax}$ = 175 + 272 = 447 mW

Using the values obtained in *Table* 76  $T_{Jmax}$  is calculated as follows:

For LQFP64, 45 °C/W

$$T_{Jmax}$$
 = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.115 °C = 102.115 °C

This is within the range of the suffix 6 version parts ( $-40 < T_{.l} < 105$  °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Section 8: Ordering information*).

Note:

With this given  $P_{Dmax}$  we can find the  $T_{Amax}$  allowed for a given device temperature range (order code suffix 6 or 7).

Suffix 6: 
$$T_{Amax} = T_{Jmax}$$
 -  $(45^{\circ}\text{C/W} \times 447 \text{ mW}) = 105\text{-}20.115 = 84.885 ^{\circ}\text{C}$   
Suffix 7:  $T_{Amax} = T_{Jmax}$  -  $(45^{\circ}\text{C/W} \times 447 \text{ mW}) = 125\text{-}20.115 = 104.885 ^{\circ}\text{C}$ 

#### **Example 2: High-temperature application**

Using the same rules, it is possible to address applications that run at high temperatures with a low dissipation, as long as junction temperature  $T_J$  remains within the specified range.

Assuming the following application conditions:

Maximum temperature  $T_{Amax}$  = 100 °C (measured according to JESD51-2),  $I_{DDmax}$  = 20 mA,  $V_{DD}$  = 3.5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$ = 0.4 V

 $P_{INTmax}$  = 20 mA × 3.5 V= 70 mW

 $P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4 \text{ V} = 64 \text{ mW}$ 

This gives: P<sub>INTmax</sub> = 70 mW and P<sub>IOmax</sub> = 64 mW:

 $P_{Dmax} = 70 + 64 = 134 \text{ mW}$ 

Thus: P<sub>Dmax</sub> = 134 mW

Using the values obtained in *Table 76* T<sub>Jmax</sub> is calculated as follows:

For LQFP64, 45 °C/W

 $T_{Jmax}$  = 100 °C + (45 °C/W × 134 mW) = 100 °C + 6.03 °C = 106.03 °C



## 8 Ordering information

For a list of available options (memory, package, and so on) or for further information on any aspect of this device, please contact your nearest ST sales office.

Table 77. Ordering information scheme 078 Example: STM32 R В **Device family** STM32 = ARM-based 32-bit microcontroller **Product type** F = General-purpose **Sub-family** 078 = STM32F078xx Pin count C = 48/49 pinsR = 64 pins V = 100 pins User code memory size B = 128 Kbyte **Package** H = UFBGA T = LQFPU = UFQFPN Y = WLCSP Temperature range  $6 = -40 \text{ to } 85 \,^{\circ}\text{C}$  $7 = -40 \text{ to } 105 \,^{\circ}\text{C}$ **Options** 



xxx = code ID of programmed parts (includes packing type)

TR = tape and reel packing blank = tray packing

## 9 Revision history

Table 78. Document revision history

Date	Revision	Changes
03-Apr-2014	1	Internal
28-May-2014	2	Initial release
17-Dec-2015	3	Cover page:  - part numbers moved to title and table of part numbers removed  - generic product name updated as STM32F078CB/RB/VB Section 2: Description:  - Figure 1: Block diagram updated Section 3: Functional overview:  - Figure 2: Clock tree updated  - Section 3.5.3: Low-power modes - added information on peripherals configurable to operate with HSI Section 4: Pinouts and pin descriptions:  - Package pinout figures updated (look and feel)  - Figure 8: WLCSP49 package pinout - now presented in top view  Section 5: Memory mapping:  - Figure 9: STM32F078CB/RB/VB memory map updated Section 6: Electrical characteristics:  - Table 20: Voltage characteristics and Table 21: Current characteristics updated  - Table 23: General operating conditions - added footnote for V <sub>IN</sub> of TTa I/O  - Table 25: Embedded internal reference voltage: added t <sub>START</sub> parameter and removed -40°-to-85° condition and associated note for V <sub>REFINT</sub> - Merger of tables 33 and 34 into Table 29: Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal  - Table 38: HSI oscillator characteristics and Figure 18: HSI oscillator accuracy characterization results for soldered parts updated  - Table 39: HSI14 oscillator characteristics: changed min values for ACC <sub>HSI14</sub> , added test conditions  - Table 47: ESD absolute maximum ratings updated  - Table 50: I/O static characteristics - note removed  - Table 55: ADC characteristics - updated some parameter values, test conditions and added footnotes (3) and (4)  - Table 55: ADC characteristics - updated some parameter values, test conditions and added footnotes (3) and (4)  - Table 59: Comparator characteristics - min added for V <sub>DDA</sub> - Figure 28: Maximum V <sub>REFINT</sub> scaler startup time from power down added